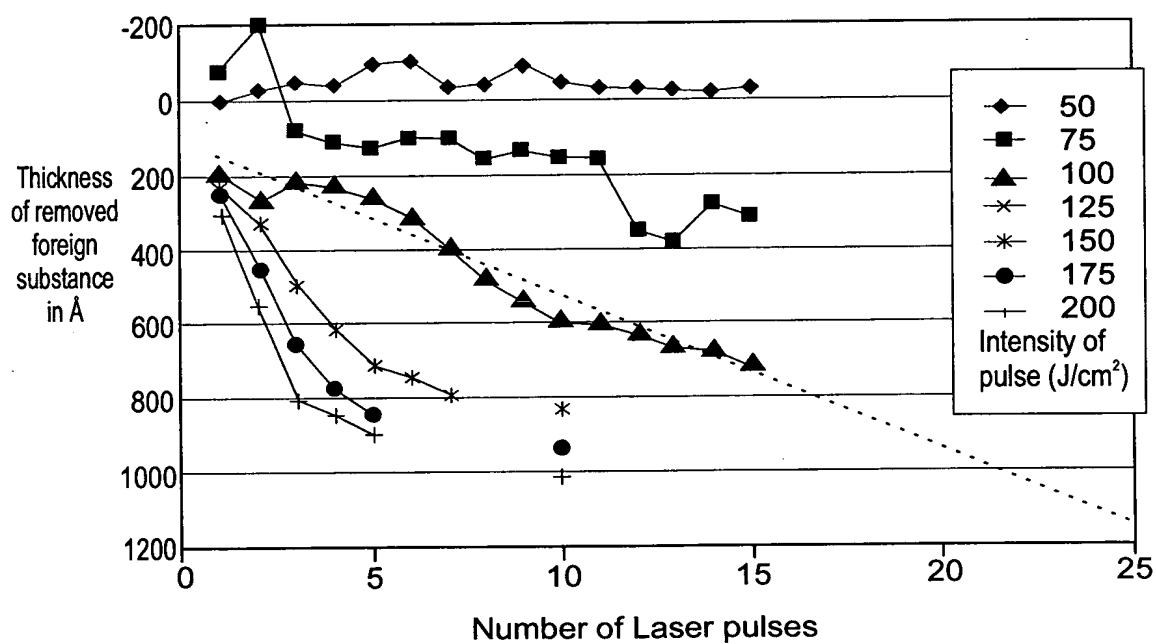


FIG. 1

BFE/PEDOT on SiNx/Glass



Laser Removal of Organic Emission Layer 150
absent Auxiliary Layers 120/130

FIG. 2
(PRIOR ART)

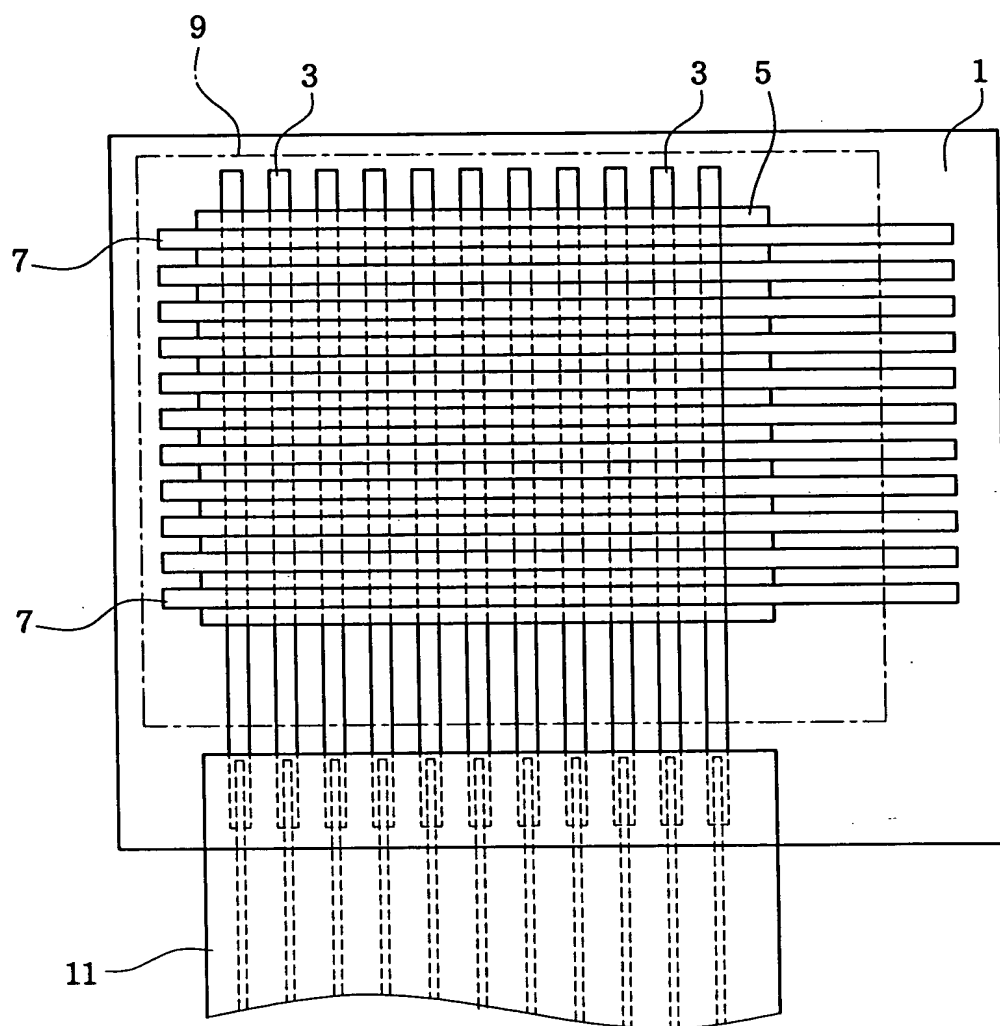


FIG. 3

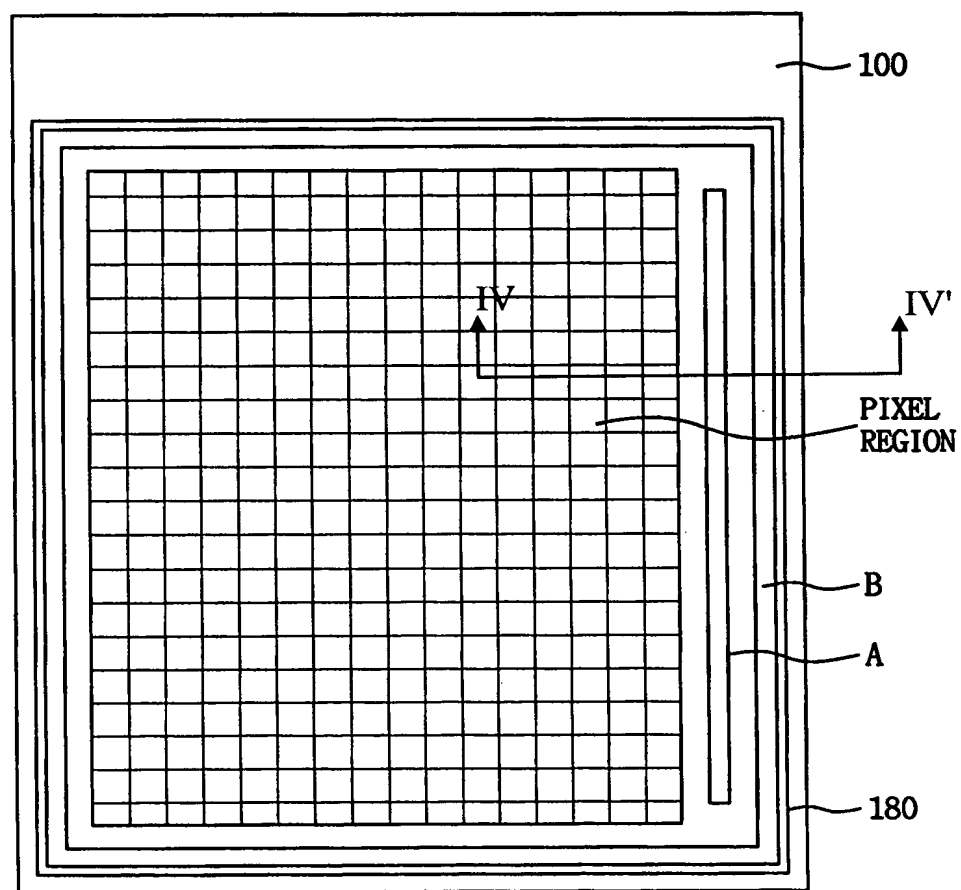


FIG. 4A

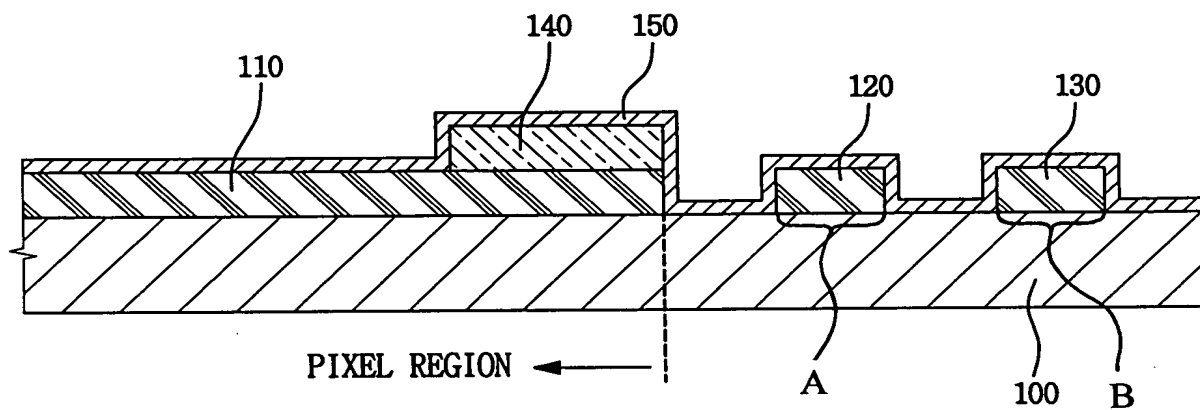
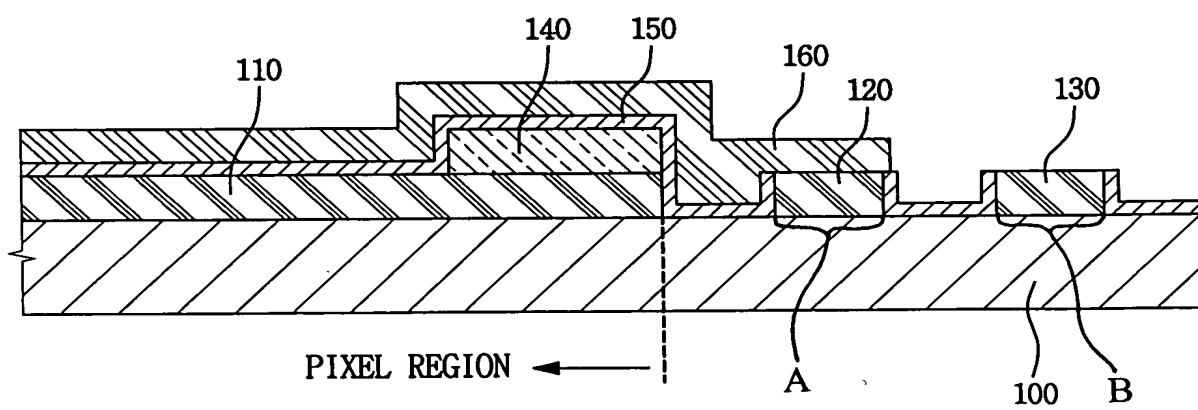


FIG. 4B

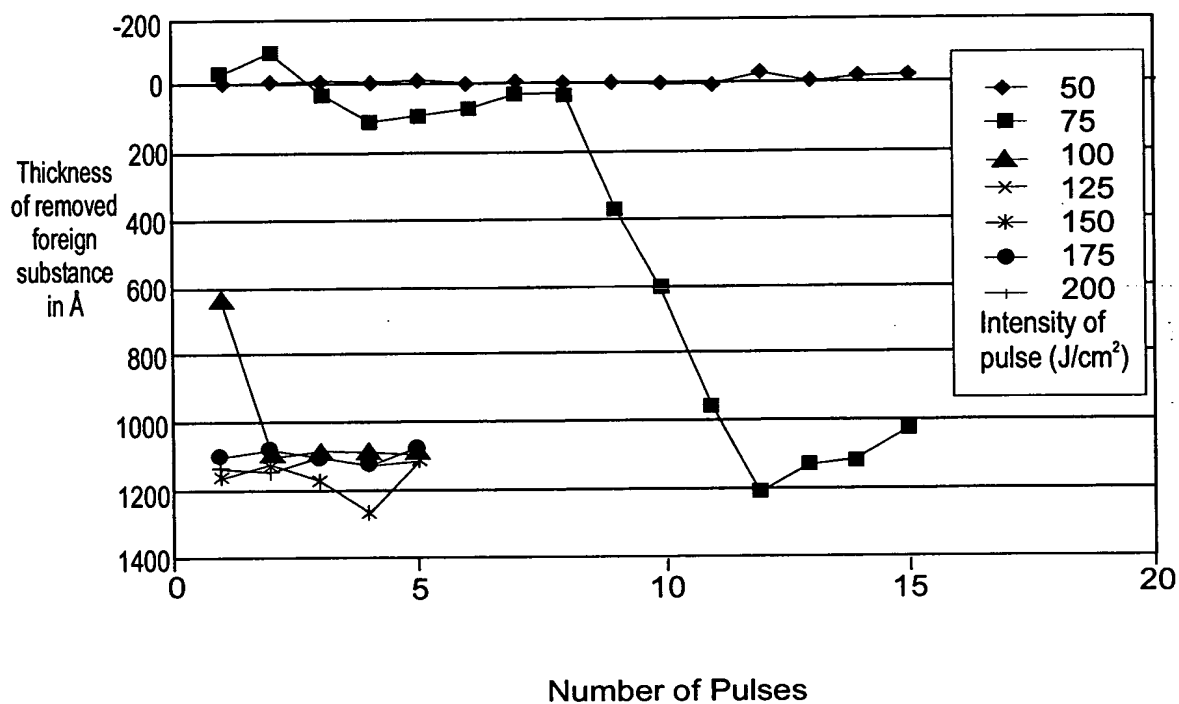


A cross-sectional view of a pixel region in a semiconductor device. The diagram shows a substrate 100 with a pixel region indicated by an arrow. The pixel region contains a gate stack 110, a source/drain region 120, and a contact 130. A passivation layer 140 is formed over the pixel region. A contact 150 is formed through the passivation layer 140 to the contact 130. A conductive layer 160 is formed over the passivation layer 140. A conductive layer 170 is formed over the conductive layer 160. A conductive layer 180 is formed over the conductive layer 170. The labels 100, 110, 120, 130, 140, 150, 160, 170, and 180 are used to identify the various layers and regions.

A cross-sectional view of a pixel region in a semiconductor device. The diagram shows a substrate 100 with a pixel region 110. A gate stack 140 is formed over the substrate. A source/drain region 150 is located adjacent to the gate stack. A contact pad 160 is formed over the source/drain region. A passivation layer 170 is formed over the contact pad. A pixel electrode 180 is formed over the contact pad. A label 'B' is located at the bottom right of the diagram.

FIG. 5

BFE/PEDOT on ITO/Glass



Laser Removal of Organic Emission Layer 150
on Auxiliary Layers 120/130

FIG. 6A

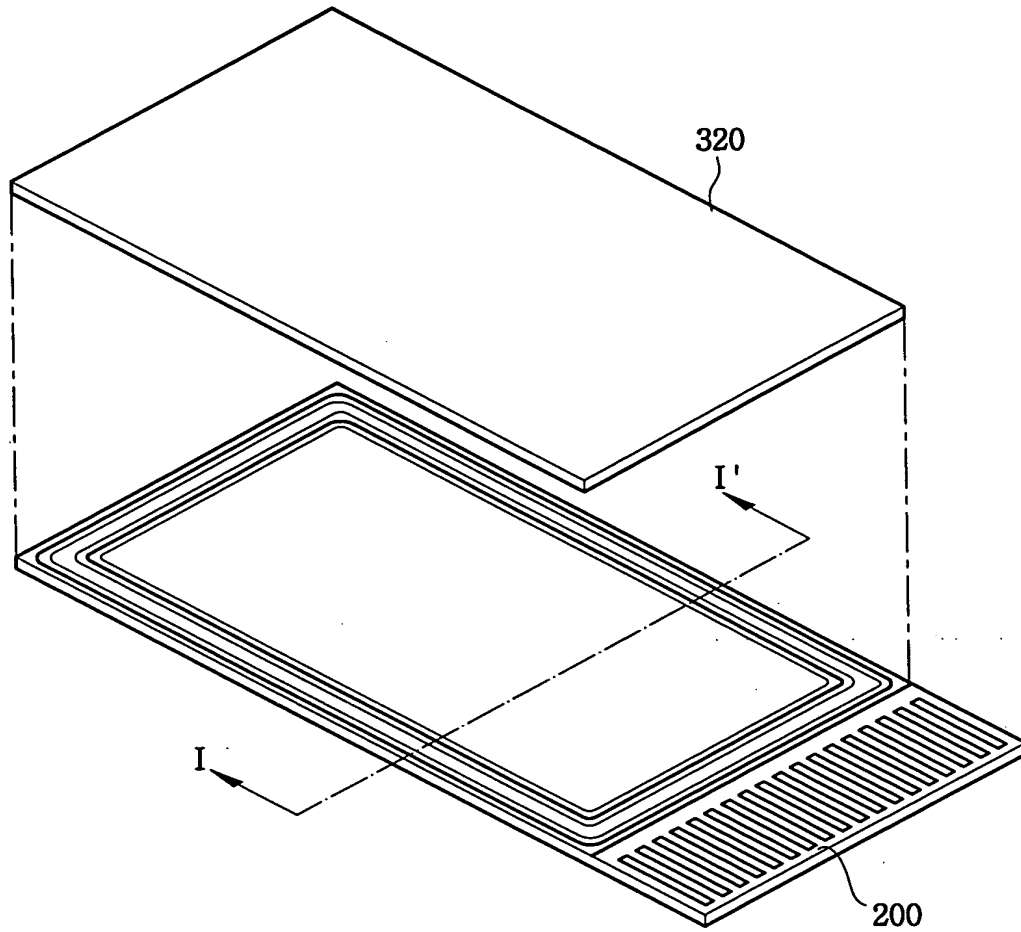


FIG. 6B

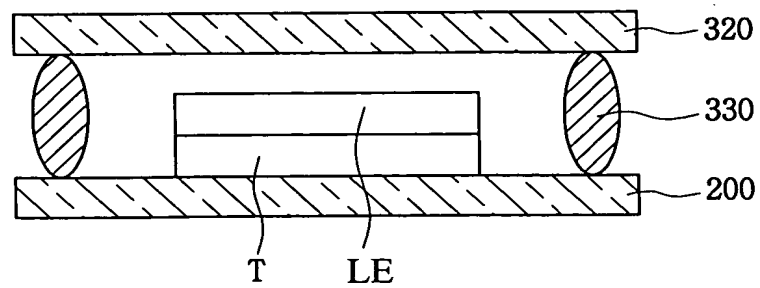


FIG. 7

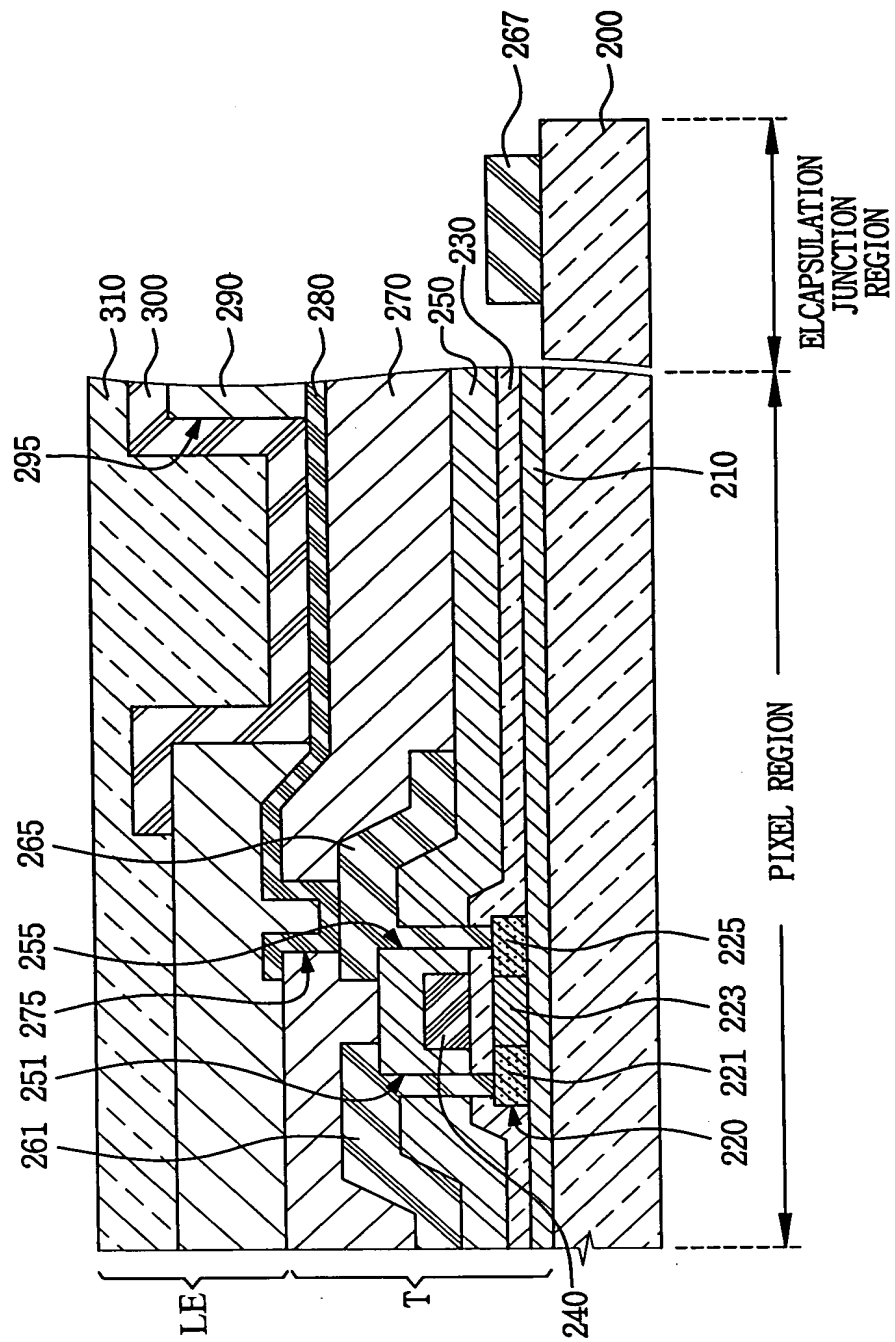


FIG. 8

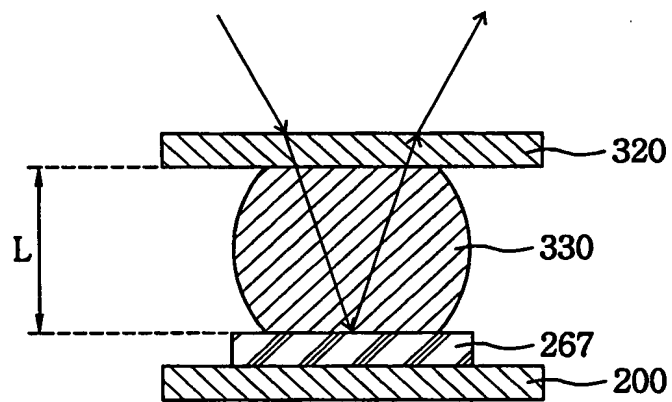


FIG. 9

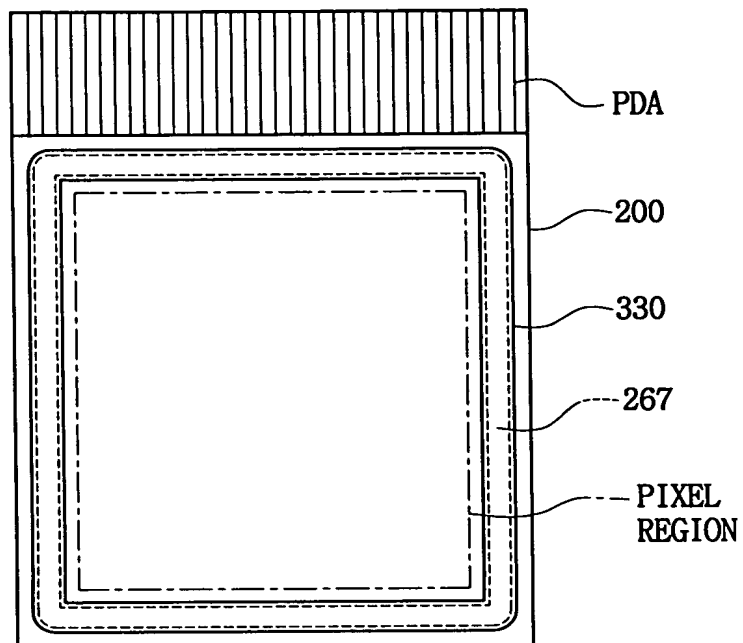


FIG. 10

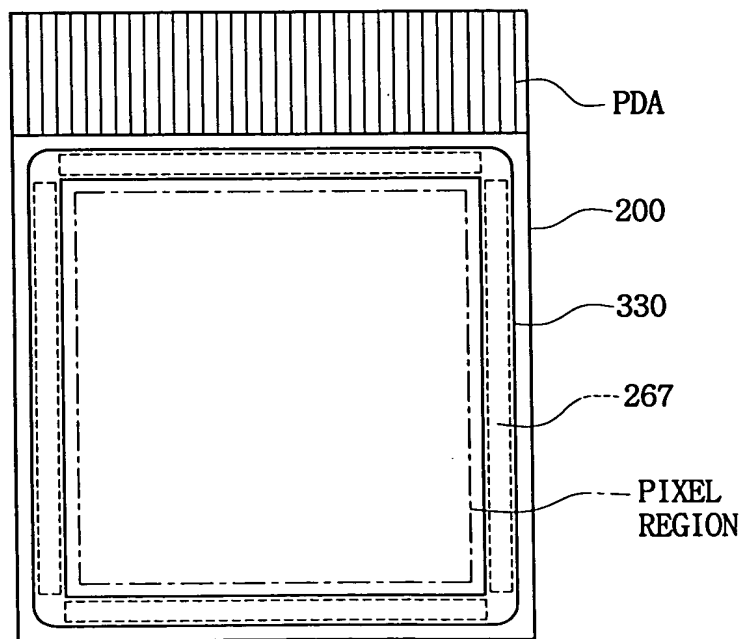


FIG. 11

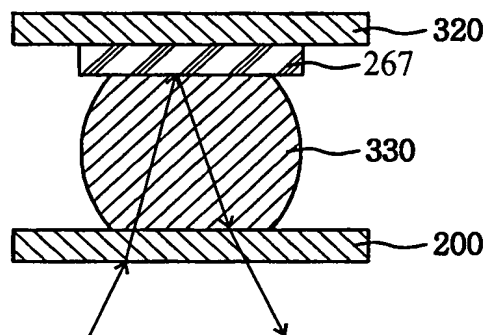


FIG. 12

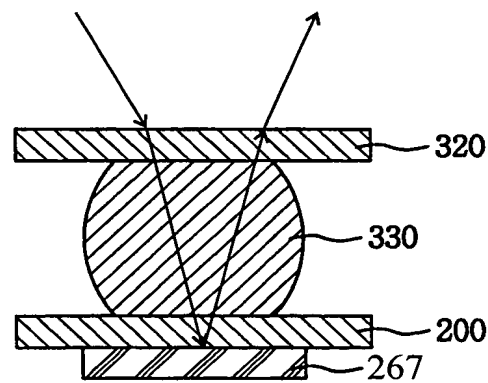


FIG. 13

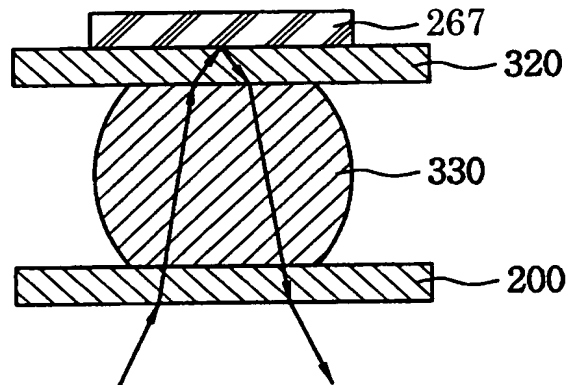


FIG. 14A

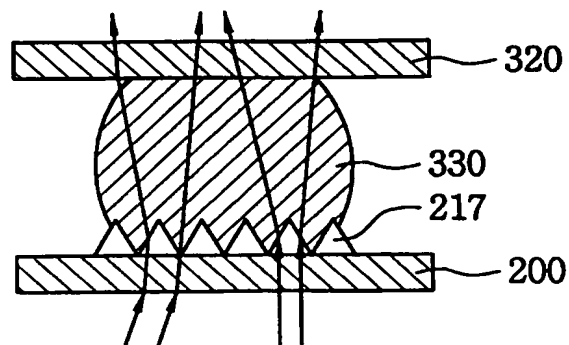


FIG. 14B

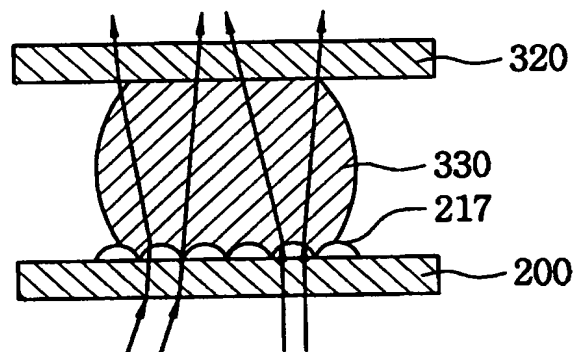


FIG. 15A

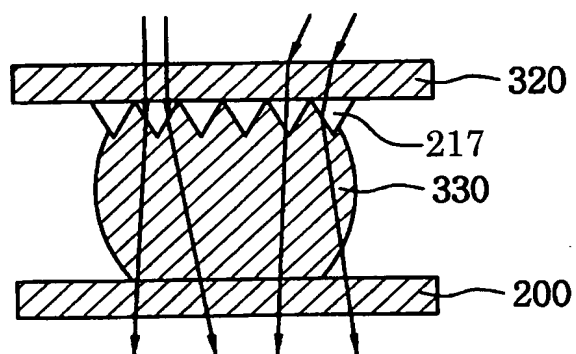


FIG. 15B

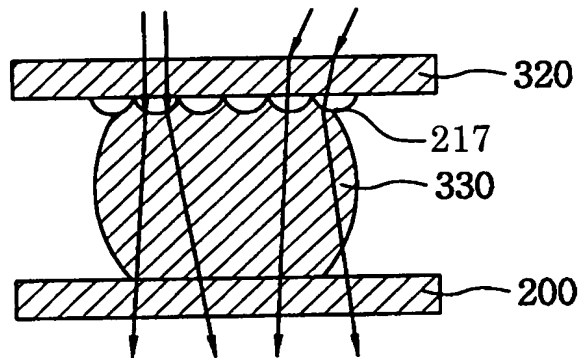


FIG. 16A

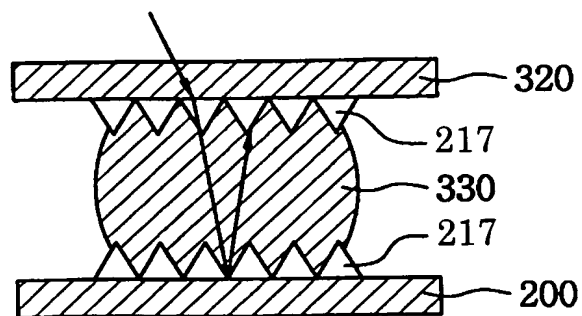


FIG. 16B

